

FDD3680

100V N-Channel PowerTrench[®] MOSFET 25A, 46mΩ

Product Overview

For complete documentation, see the data sheet.

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable RDS(ON) specifications. The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 25 A, 100 V.
- RDS(ON) = 46 mΩ @ VGS = 10 V
- RDS(ON) = 51 mΩ @ VGS = 6 V
- Low gate charge (38 nC typical)
- Fast switching speed
- High performance trench technology for extremely RDS(ON)
- High power and current handling capability

Applications

- This product is general usage and suitable for many different applications.